

AMENDMENTS

IN THE CLAIMS:

1. (Currently Amended) A power semiconductor module comprising a plurality of semiconductor components situated on a substrate, wherein

- the substrate ~~has~~ is divided into a plurality of separate substrate regions and
- one or a plurality of connecting regions are situated between adjacent substrate regions, wherein said connecting region are designed such that via which connecting regions a movement of the one substrate regions does not translate to an adjacent substrate region are connected such that they can move relative to one another.

2. (Currently Amended) The power semiconductor module as claimed in claim 1, wherein

- the connecting regions are formed by recesses in ~~the material of the substrate~~ a module housing enclosing said substrate regions.

3. (Original) The power semiconductor module as claimed in claim 2, wherein

- the material recesses are slotted.

4. (Original) The power semiconductor module as claimed in claim 1, wherein

- the substrate is a ceramic.

5. (Original) The power semiconductor module as claimed in claim 2, wherein

- the substrate is a ceramic.

6. (Original) The power semiconductor module as claimed in claim 3, wherein

- the substrate is a ceramic.

7. (Canceled)

8. (Currently Amended) The power semiconductor module as claimed in claim 2, wherein
 - the module housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.
9. (Currently Amended) The power semiconductor module as claimed in claim 3, wherein
 - the module housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.
10. (Canceled)
11. (Original) The power semiconductor module as claimed in claim 5, wherein
 - the housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.
12. (Original) The power semiconductor module as claimed in claim 6, wherein
 - the housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.
13. (Original) The power semiconductor module as claimed in claim 1, wherein
 - the power semiconductor module has a housing, which, in the region between the substrate regions, has action points for a mechanical pressure application of the connecting regions, and
 - the housing applies pressure to the individual substrate regions.
14. (NEW) A power semiconductor module comprising
 - a plurality of substrate elements having top and bottom surface, each substrate element comprising a semiconductor component arranged on the top surface of a substrate element;
 - one or a plurality of connecting regions arranged between adjacent substrate regions to form a continuous bottom surface, wherein said connecting region are designed such that a movement of one substrate regions does not translate to an adjacent substrate region.

15. (NEW) The power semiconductor module as claimed in claim 14, further comprising a module housing enclosing said plurality of substrate elements.
16. (NEW) The power semiconductor module as claimed in claim 15, wherein
 - the connecting regions are formed by recesses in the module housing.
17. (NEW) The power semiconductor module as claimed in claim 16, wherein
 - the material recesses are slotted.
18. (NEW) The power semiconductor module as claimed in claim 14, wherein
 - the substrate is a ceramic.
19. (NEW) The power semiconductor module as claimed in claim 15, wherein
 - the module housing, at least in the regions of the substrate elements, is such that it acts on the substrate elements with a spring force.
20. (NEW) The power semiconductor module as claimed in claim 14, further comprising
 - a heat sink having a flat surface, wherein the continuous bottom surface of the plurality of substrate elements is arranged on said flat surface.
21. (NEW) The power semiconductor module as claimed in claim 15, wherein
 - the module housing in the region between the substrate elements comprises action points for a mechanical pressure application of the connecting regions, and
 - the housing applies pressure to the individual substrate elements.

In the Specification:

Please replace the paragraph [0035] on page 8 with the following paragraph:

[0035] Besides the substrate regions 3, 4, and 5 the ~~substrate-2~~ **module housing 20** has connecting regions 30 and 31 formed between the substrate regions (also cf. figure 2). The substrate regions 3 and 4 are connected such that they can move relative to one another e.g. via the connecting region 30. The connecting region 30 functions as it were as an articulated joint or hinge, so that the substrate regions 3 and 4 can also be oriented with respect to one another to form an angle other than ~~180°~~ **180°**(correction angle). By way of example, this prevents a deformation of the substrate region 3 from continuing into the substrate region 4. By way of example, if the substrate region 3 is tilted through an angle ~~α~~ **α** (illustrated in greatly enlarged and exaggerated fashion in figure 1) with respect to the horizontal H due to deformations on account of thermally induced stresses, it is possible, by correspondingly tilting the substrate region 4 in the opposite sense, to avoid a propagation of said angle α into the substrate region 4 and even to compensate for the tilting by means of an equal and opposite tilting. A module underside 25 which is free to the greatest possible extent from deformations manifested on account of thermally induced stresses is thus provided as contact area of the power semiconductor module.

Please replace the paragraph [0036] on page 9 with the following paragraph:

[0036] According to figure 2, by way of example, the connecting regions 30 and 31 are formed by slots 33, 34 introduced into the material of the **module housing 20**~~initial-substrate~~. However, other geometrical forms and configurations of the connecting regions are also conceivable, which in the same way effect an increased flexibility of the connecting regions with respect to the **module housing 20**~~initial-substrate~~.